FH0106

N-Channel Enhancement Mode MOSFET

Description

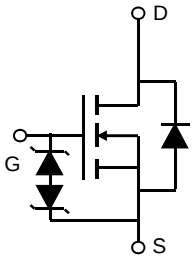
The FH0106 is the N-Channel enhancement mode MOSFET in a plastic package (SOT-23) using the Trench technology.It is ESD protected.

Applications

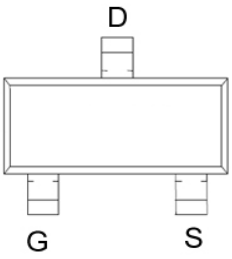
- LED Lighting Application,
- ON/OFF switch
- Networking

Features

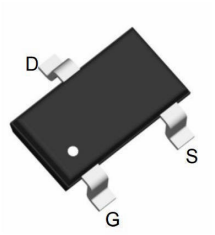
- V_{DS} = 60V ; V_{GS} = ±20 V ; I_D = 0.7A
  $R_{DS(ON)}$(Typ.)= 1 Ω @V_{GS} = - 10V
  $R_{DS(ON)}$(Typ.)= 1.3 Ω @V_{GS} = - 4.5V
  $R_{DS(ON)}$(Typ.)= 1.6 Ω @V_{GS} = - 3.3V
- Low $R_{DS(on)}$ @V_{GS}=10V
- 3.3V Logic Level Control
- N Channel SOT-23 Package
- HMB ESD Protection 2KV
- Pb−Free, RoHS Compliant



Schematic diagram



Marking and Pin Assignment



SOT-23 top view

■ Order Information

Product	Package	Marking	Packing
FH0106	SOT-23	SS	3000PCS/Reel

■ Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter		Rating	Unit
Common Ratings (T_A=25°C Unless Otherwise Noted)				
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		60	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-50 to 150	°C
Mounted on Large Heat Sink				
I_D	Continuous Drain Current	T_A=25°C	0.7	A
		T_A=70°C	0.45	
I_{DM}	Pulse Drain Current Tested①	T_A=25°C	1.8	A
P_D	Maximum Power Dissipation	T_A=25°C	0.3	W
		T_A=70°C	0.2	
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		400	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(T_A=25℃)	V_{DS}=60V, V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T_A=125℃)	V_{DS}=48V, V_{GS}=0V	--	--	100	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	--	--	±10	uA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.6	1.0	1.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=10V, I_D=0.5A	--	1.0	1.5	Ω
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=4.5V, I_D=0.3A	--	1.3	2	Ω
$R_{DS(ON)}$	Drain-Source On-State Resistance②	V_{GS}=3.3V, I_D=0.2A	--	1.6	3	Ω
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=30V, V_{GS}=0V, f=1MHz	--	23.8	--	pF
C_{oss}	Output Capacitance		--	3.9	--	pF
C_{rss}	Reverse Transfer Capacitance		--	1.5	--	pF
Q_g	Total Gate Charge	V_{DS}=30V I_D=0.5A, V_{GS}=10V	--	0.93	--	nC
Q_{gs}	Gate Source Charge		--	0.18	--	nC
Q_{gd}	Gate Drain Charge		--	0.31	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn on Delay Time	V_{DD}=30V, I_D=0.3A, R_G=3.3Ω, V_{GS}=10V	--	6	--	ns
t_r	Turn on Rise Time		--	3.5	--	ns
$t_{d(off)}$	Turn Off Delay Time		-	20	--	ns
t_f	Turn Off Fall Time		--	5.9	--	ns
Source Drain Diode Characteristics						
I_{SD}	Source drain current(Body Diode)	T_A=25℃	--	--	0.4	A
V_{SD}	Forward on voltage②	T_j=25℃, I_{SD}=0.5A, V_{GS}=0V	--	0.78	1.2	V

Notes: ① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

Typical Characteristics

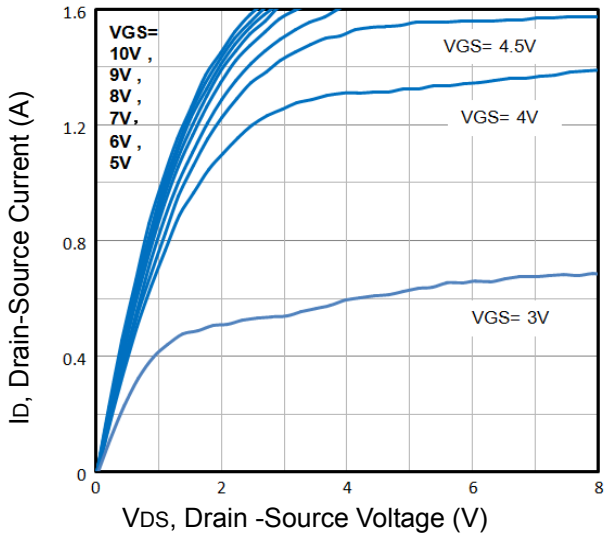


Fig1. Typical Output Characteristics

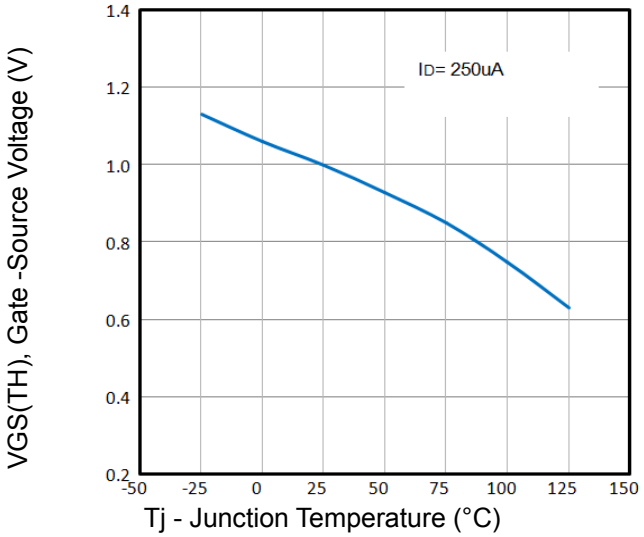


Fig2. Normalized Threshold Voltage Vs. Temperature

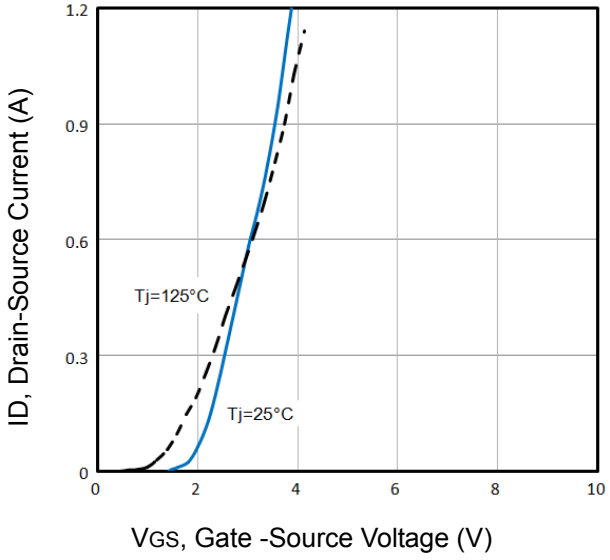


Fig3. Typical Transfer Characteristics

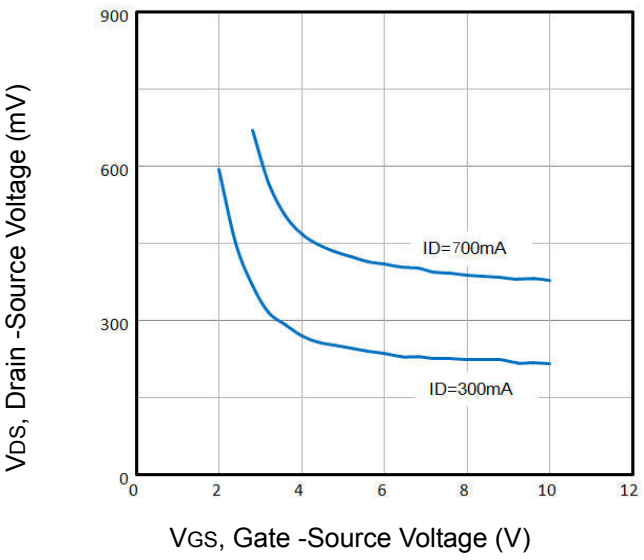


Fig4. Drain -Source Voltage vs Gate -Source Voltage

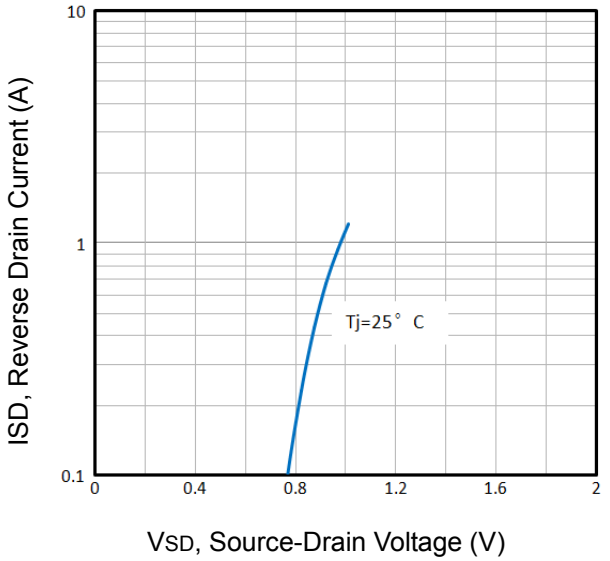


Fig5. Typical Source-Drain Diode Forward Voltage

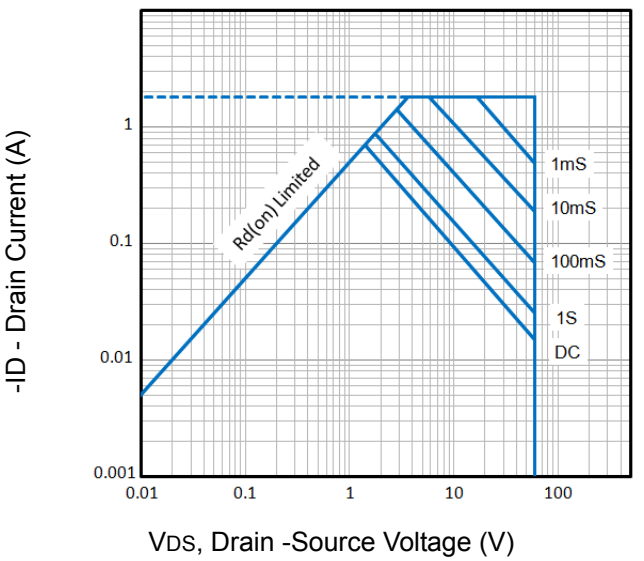


Fig6. Maximum Safe Operating Area

Typical Characteristics

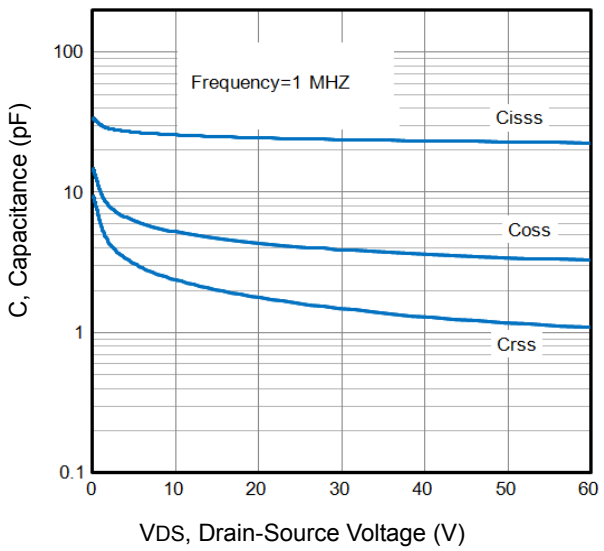


Fig7. Typical Capacitance Vs. Drain-Source Voltage

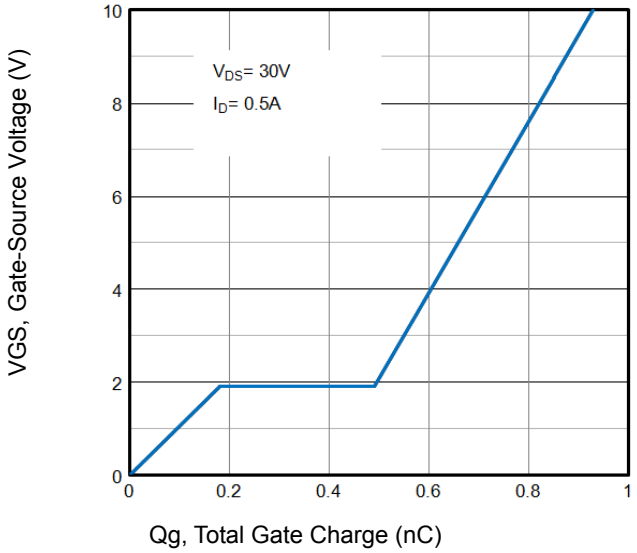


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

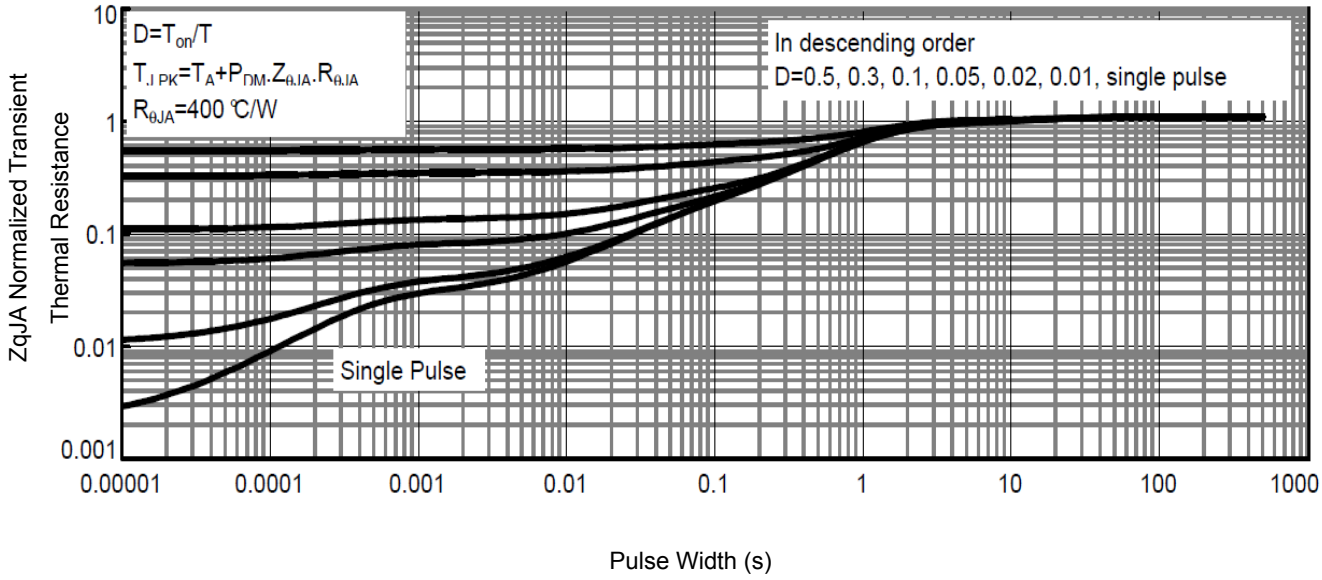


Fig9. Normalized Maximum Transient Thermal Impedance

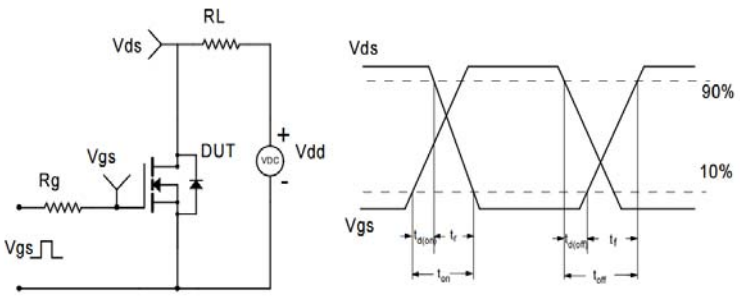
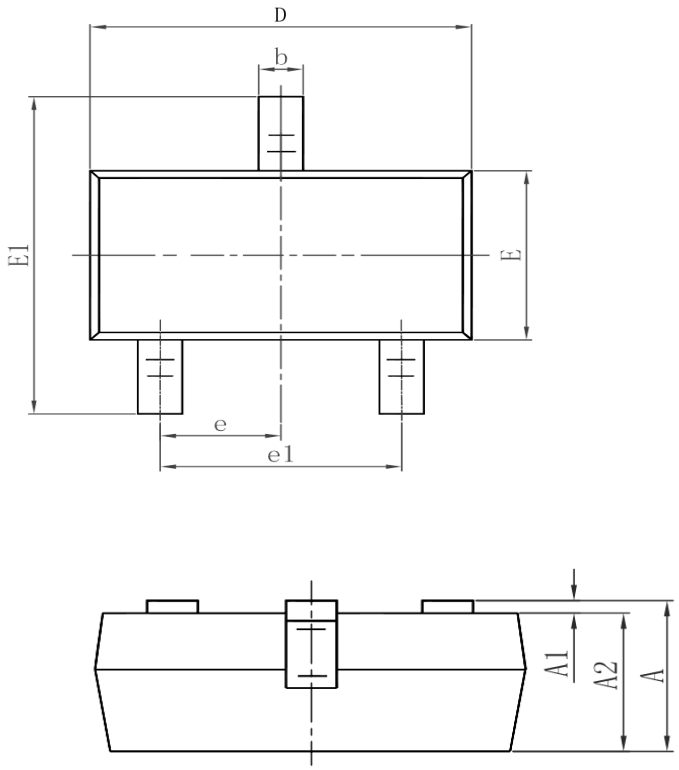


Fig10. Switching Time Test Circuit and waveforms

■ Package Dimensions : SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°